

Supplementary Information

Growth of single crystalline films on lattice-mismatched substrates through 3D to 2D mode transition

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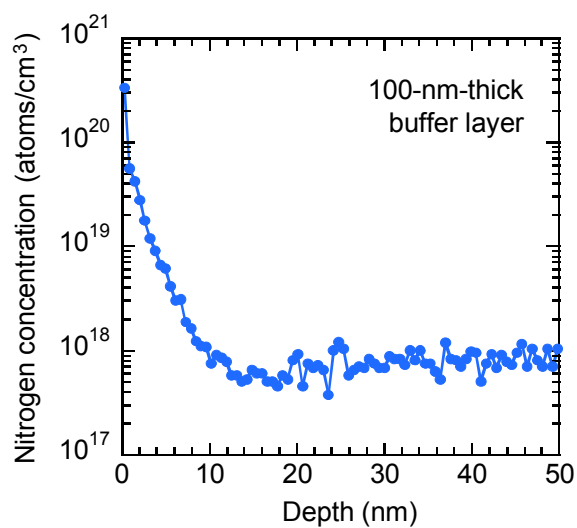


Figure S1. The depth profile of nitrogen concentration of a buffer layer, measured by secondary ion mass spectroscopy (SIMS). Here the film thickness is 100 nm. The segregation width is less than 10 nm, taking into account of knock-on effect in which atoms of the sample are driven deeper into the sample during the sputtering process by the primary ion beam used for analysis.